

## BLV57

# NPN SILICON RF POWER TRANSISTOR

### DESCRIPTION:

**BLV57** is Designed for use as push-pull amplifier, primarily in linear UHF TV transmitting Applications.

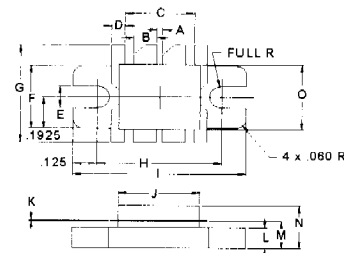
### FEATURES:

- Input Matching Network
- Common emitter
- **Omnigold™** Metalization System with eutectic die bonding

### MAXIMUM RATINGS

$I_C$	2.0 A
$V_{CESM}$	50 V
$V_{CE}$	27 V
$P_{DISS}$	77 W @ $T_C = 25^\circ C$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	2.27 °C/W

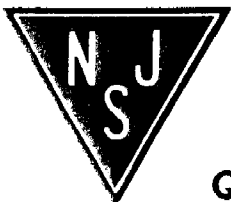
### PACKAGE STYLE .400 8L FLG



DIM	MINIMUM mm (in)	MAXIMUM mm (in)
A	.030 / 0.76	
B	.115 / 2.92	.125 / 3.18
C	.360 / 9.14	
D	.065 / 1.65	.075 / 1.91
E	.130 / 3.30	
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

### CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 25\text{ mA}$	27			V
$BV_{CES}$	$I_C = 10\text{ mA}$	50			V
$BV_{EBO}$	$I_E = 5.0\text{ mA}$	3.5			V
$I_{CES}$	$V_E = 27\text{ V}$			10	mA
$h_{FE}$	$V_{CE} = 25\text{ V}$ $I_C = 850\text{ mA}$	15			---
$f_T$	$V_{CB} = 25\text{ V}$ $I_E = 1.7\text{ A}$		2.5		GHz
	$V_{CB} = 25\text{ V}$ $I_E = 850\text{ mA}$		2.5		
$P_G$ $IMD_1$	$V_{CE} = 25\text{ V}$ $P_{OUT} = 6.0\text{ W}$	8.0			dB dBc
	$I_C = 850\text{ mA}$ $f = 860\text{ MHz}$	-60			



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